# **Preliminary**

TOSHIBA Photocoupler GaAlAs IRED + Photo IC

# **TLP350**

Inverter for Air Conditioner IGBT/Power MOS FET Gate Drive Industrial Inverter

The TOSHIBA TLP350 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

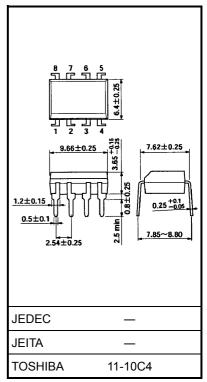
TLP350 is suitable for gate driving circuit of IGBT or power MOS FET..

- Peak output current:  $I_0 = \pm 2.0 \text{ A (max)}$
- Guaranteed performance over temperature: -40 to 100°C
- Supply current:Icc = 2 mA (max)
- Power supply voltage:  $V_{CC} = 15$  to 30 V
- Threshold input current : IFLH = 5 mA (max)
- Switching time  $(t_{pLH}/t_{pHL})$ : 500 ns (max)
- Common mode transient immunity: 15 kV/µs
- Isolation voltage: 3750 Vrms

#### **Truth Table**

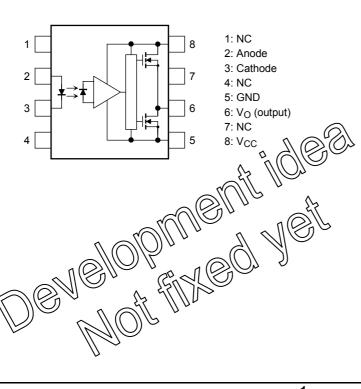
Input	LED	Tr1	Tr2	Output
Н	ON	ON	OFF	Н
L	OFF	OFF	ON	L

#### Unit: mm

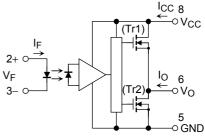


Weight: 0.54 g (typ.)

#### Pin Configuration (top view)



#### **Schematic**



A 0.1 µF bypass capacitor must be connected between pin 8 and 5. (See Note 6)

#### Maximum Ratings (Ta = 25°C)

	Characteristics	Symbol	Rating	Unit	
	Forward current	lF	20	mA	
	Forward current derating (Ta ≥ 85°C)	$\Delta I_{F}/\Delta Ta$	-0.54	mA/°C	
LED	Peak transient forward current	(Note 1)	I <sub>FP</sub>	1	Α
	Reverse voltage		V <sub>R</sub>	5	V
	Junction temperature		Tj	125	°C
	"H" peak output current	(Note 2)	I <sub>OPH</sub>	-2.0	Α
ō	"L" peak output current	(Note 2)	I <sub>OPL</sub>	2.0	Α
Detector	Output voltage	(Note 3)	Vo	35	V
۵	Supply voltage	(Note 3)	V <sub>CC</sub>	35	V
	Junction temperature		Tj	125	°C
Ope	rating frequency	(Note 4)	f		kHz
Storage temperature range			T <sub>stg</sub>	-55 to 125	°C
Operating temperature range		T <sub>opr</sub>	-40 to 100	°C	
Lead soldering temperature (10 s) (Note 5)		T <sub>sol</sub>	260	°C	
Isola	tion voltage (AC, 1 minute, R.H. ≤ 60%)	(Note 6)	BVS	3750	Vrms

Note 1: Pulse width  $P_W \le 1 \mu s$ , 300 pps

Note 2: Exponential waveform pulse width  $P_W \le \mu s$ ,  $f \le kHz$ 

Note 3: Ta ≤ 100 °C

Note 4: Exponential waveform  $I_{OPH} \le A (\le \mu s)$ ,  $I_{OPL} \le + A (\le \mu s)$ ,  $T_{OPL} \le + A (\le \mu s)$ 

Note 5: It is 2 mm or more from a lead root.

Note 6: Device considerd a two terminal device: pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Note 7: A ceramic capacitor( $0.1 \, \mu F$ ) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

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#### **Recommended Operating Conditions**

Characteristics		Symbol	Min	Тур.	Max	Unit
Input current, ON	(Note 8)	I <sub>F (ON)</sub>	7.5		10	mA
Input voltage, OFF		V <sub>F (OFF)</sub>	0	_	0.8	V
Supply voltage		V <sub>CC</sub>	15	_	30	V
Peak output current		I <sub>OPH</sub> /I <sub>OPL</sub>	_	_	±1.0	Α
Operating temperature		T <sub>opr</sub>	-40	_	100	°C

Note 8: Input signal rise time (fall time)  $< 0.5 \mu s$ .

### Electrical Characteristics (Ta = -40 to 100°C, unless otherwise specified)

Characteristics		Symbol	Test Circuit	Test (	Condition	Min	Typ.*	Max	Unit
Forward voltage		V <sub>F</sub>	_	$I_F = 5 \text{ mA}, \text{ Ta} = 25^{\circ}\text{C}$		_	1.55	1.70	V
Temperature coefficient of forward voltage		ΔV <sub>F</sub> /ΔTa	_	I <sub>F</sub> = 5 mA		_	-2.0	_	mV/°C
Input reverse current		I <sub>R</sub>	_	V <sub>R</sub> = 5 V, Ta = 2	V <sub>R</sub> = 5 V, Ta = 25°C		_	10	μΑ
Input capacitance		C <sub>T</sub>	_	V = 0 , f = 1 MHz	,Ta = 25°C	_	45	_	pF
	"H" Level	I <sub>OPH1</sub>	1	V <sub>CC</sub> = 30 V	V <sub>8-6</sub> = 4.0 V	-1.0	-1.5	_	
Output current	n Level	I <sub>OPH2</sub>	] '	$I_F = 5 \text{ mA}$	V <sub>8-6</sub> =			_	A
(Note 9)	"L" Level	I <sub>OPL1</sub>	2	V <sub>CC</sub> = 30 V I <sub>F</sub> = 0 mA	V <sub>6-5</sub> = 2.0 V	1.0	2.0	_	7 ^
	L Level	I <sub>OPL2</sub>	2		V <sub>6-5</sub> =			_	
	"H" Level	V <sub>OH</sub>	3	V <sub>CC 1</sub> = +15 V	$I_O = -100 \text{ mA},$ $I_F = 5 \text{ mA}$	11		_	V
Output voltage	"L" Level	V <sub>OL</sub>	4	V <sub>EE 1</sub> = -15 V	$I_O = 100 \text{ mA},$ $V_F = 0.8 \text{ V}$	_		1.0	V
Complete	"H" Level	Іссн	5	V <sub>CC</sub> = 30 V	I <sub>F</sub> = 10 mA	_		2.0	^
Supply current	"L" Level	I <sub>CCL</sub>	6	V <sub>O</sub> open	I <sub>F</sub> = 0 mA	_		2.0	mA
Threshold input current	$L \rightarrow H$	I <sub>FLH</sub>	_	V <sub>CC 1</sub> = +15 V V <sub>EE 1</sub> = -15 V, V <sub>O</sub> > 0 V		_		5	mA
Threshold input voltage	$H \rightarrow L$	V <sub>FHL</sub>		V <sub>CC 1</sub> = +15 V V <sub>EE 1</sub> = -15 V, V <sub>O</sub> < 0 V		0.8	_	_	٧
Supply voltage		V <sub>CC</sub>		_		15		30	V
UVLO thresh hold		V <sub>UVLO+</sub>	_	V <sub>O</sub> > 2.5 V , I <sub>F</sub> = 5 mA ,		11.0		13.5	V
		V <sub>UVLO-</sub>	_	I <sub>O</sub> =100 mA	9.5		12.0	V	

<sup>\*:</sup> All typical values are at Ta = 25°C

Note 9: Duration of I<sub>O</sub> time  $\leq$  50  $\mu$ s

Note 10: This product is more sensitive than the conventional product to static electricity (ESD) because of a lowest power consumption design.

General precaution to static electricity (ESD) is necessary for handling this component.

### Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0,f = 1MHz (Note6	) —	8.0	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, Ta = 25°C,	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
Isolation resistance		R.H. ≤ 60% (Note6)				
		AC,1 minute	3750	_	_	V
Isolation voltage	$BV_S$	AC,1 second,in oil	_	10000	_	V <sub>rms</sub>
		DC,1 minute,in oil	_	10000	_	Vdc

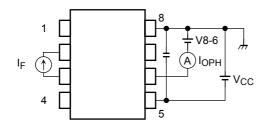
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### Switching Characteristics (Ta = -40 to $100^{\circ}$ C, unless otherwise specified)

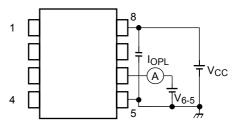
Characteristics		Symbol	Test Circuit	Test Co	ndition	Min	Typ.*	Max	Unit
Propagation delay time	$L \rightarrow H$	t <sub>pLH</sub>		V <sub>CC 1=</sub> +15 V V <sub>FF 1=</sub> -15 V	$I_F=0 \rightarrow 5 \; mA$	50	250	500	20
	$H \rightarrow L$	t <sub>pHL</sub>		P = 20 O	$I_F = 5 \rightarrow 0 \text{ mA}$	50	250	500	ns
Propagation delay difference between any two parts or channels		PDD  t <sub>pHL</sub> -t <sub>pLH</sub>	7	$V_{CC}$ 1= +15 V , $V_{EE}$ 1= -15 V, $R_g$ = 20 $\Omega$ , $C_q$ = 10 nF		_	_	450	ns
Output rise time (10-90%)		t <sub>r</sub>		V <sub>CC 1</sub> = +15 V V <sub>FF 1</sub> = -15 V	$I_F=0 \rightarrow 5 \ mA$	_			
Output fall time (90-10%)		t <sub>f</sub>		$R_{g} = 20 \Omega$ $C_{q} = 10 \text{ nF}$	$I_F = 5 \rightarrow 0 \text{ mA}$	_		_	ns
Common mode transient immunity at hight level output		CM <sub>H</sub>	0	3	I <sub>F</sub> = 5 mA V <sub>O (min)</sub> =26V	-15000		_	V/μs
Common mode transient immunity at low level output		CML	0	V <sub>CC</sub> = 30 V	$I_F = 0 \text{ mA}$ $V_{O \text{ (max)}} = 1V$	15000			ν/μ5

<sup>\*:</sup> All typical values are at Ta = 25°C

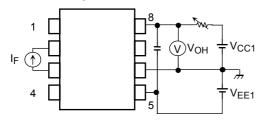
#### Test Circuit 1: I<sub>OPH</sub>



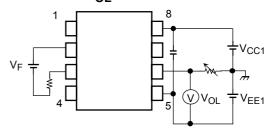
#### Test Circuit 2: I<sub>OPL</sub>



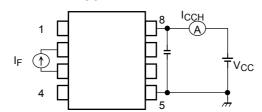
Test Circuit 3: V<sub>OH</sub>



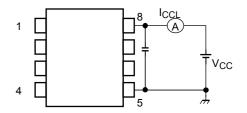
Test Circuit 4: V<sub>OL</sub>



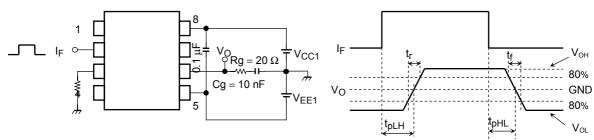
Test Circuit 5: I<sub>CCH</sub>



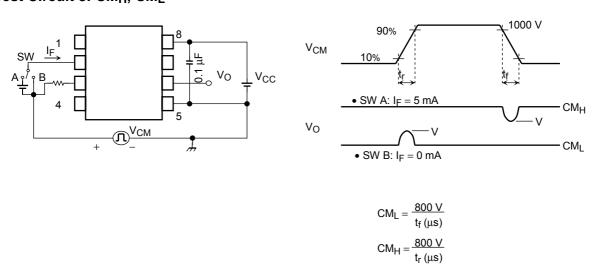
Test Circuit 6: I<sub>CCL</sub>



### Test Circuit 7: t<sub>pLH</sub>, t<sub>pHL</sub>, t<sub>r</sub>, t<sub>f</sub>, PDD



# Test Circuit 8: CM<sub>H</sub>, CM<sub>L</sub>



 $\mathrm{CM_L}$  (CMH) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

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